
2SC458(K)

Silicon NPN Epitaxial

HITACHI

Application

- Low frequency amplifier
- Medium speed switching

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SC458 (K)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	30	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Emitter current	I_E	-100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

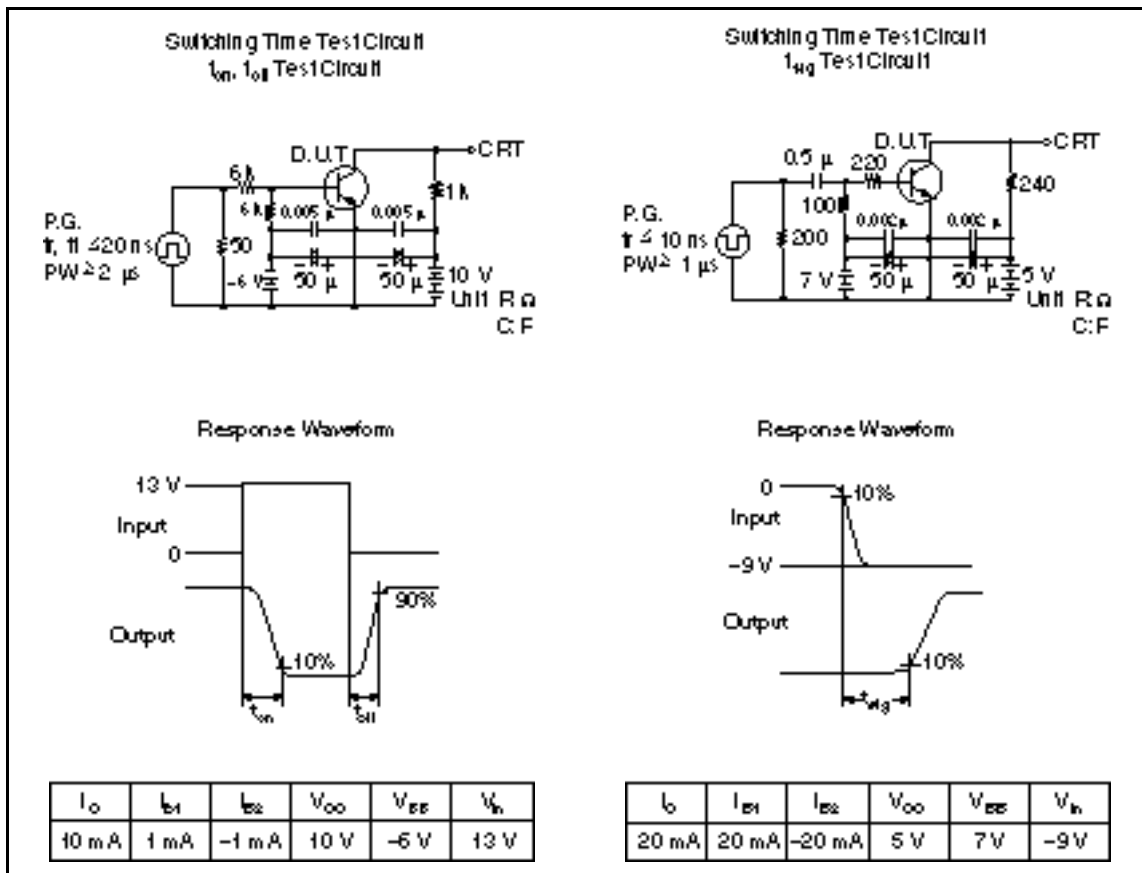
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 18 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	1.0	μA	$V_{EB} = 4 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	500		$V_{CE} = 1 \text{ V}, I_C = 10 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.4	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	$V_{BE(sat)}$	—	—	1.0	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Gain bandwidth product	f_T	100	—	—	MHz	$V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$
Collector output capacitance	C_{ob}	—	—	4	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Turn on time	t_{on}	—	80	—	ns	$I_C = 10 \text{ mA}, I_{B1} = -10 \text{ mA}, I_{B2} = 10 \text{ mA}, V_{CC} = 10 \text{ V}$
Turn off time	t_{off}	—	300	—	ns	
Storage time	t_{stg}	—	260	—	ns	$I_C = I_{B1} = -I_{B2} = 20 \text{ mA}, V_{CC} = 5 \text{ V}$

Note: 1. The 2SC458 (K) is grouped by h_{FE} as follows.

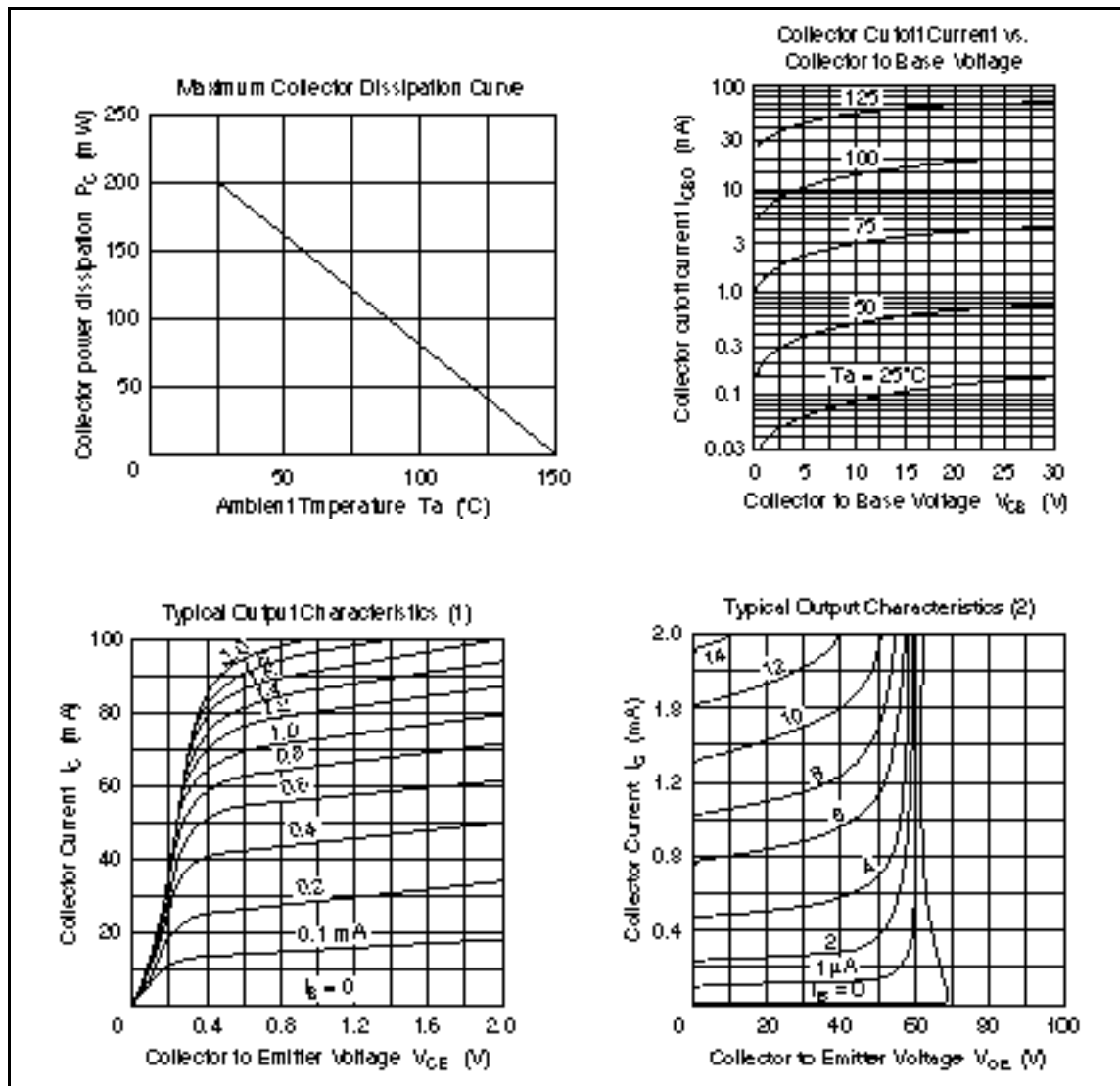
B	C	D
100 to 200	160 to 320	250 to 500

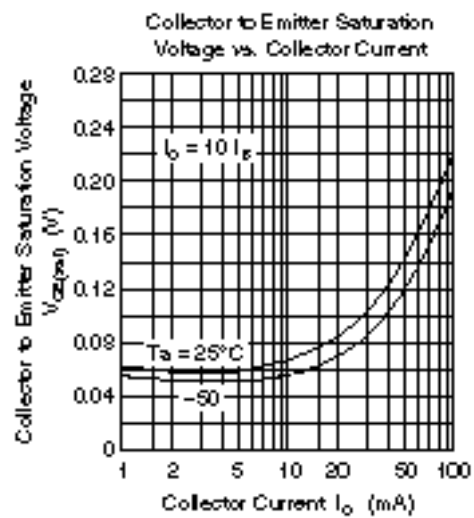
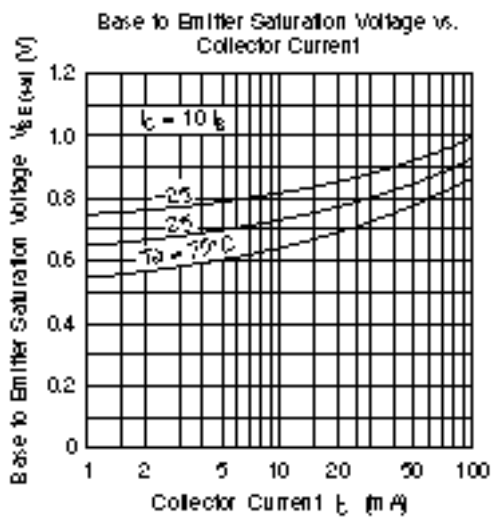
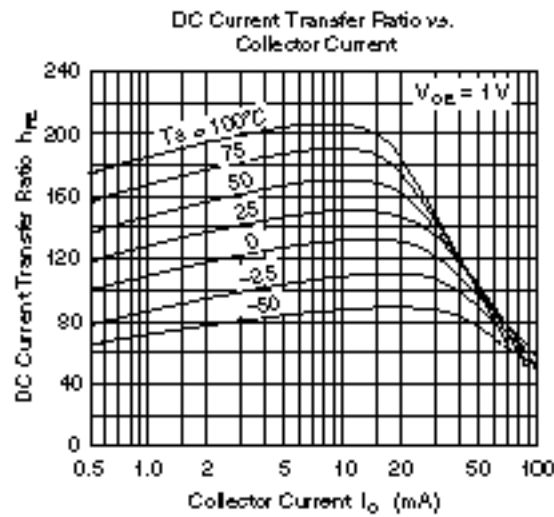
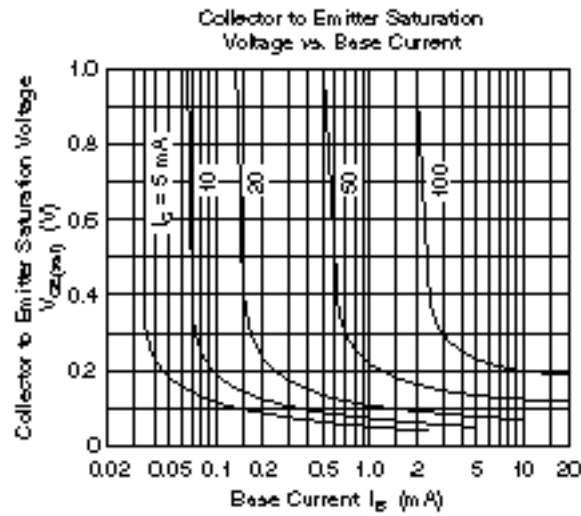
Small Signal h Parameters

Item	Symbol	Typ	Unit	Test conditions
Input impedance	h_{ie}	16.5	k	$V_{CE} = 5\text{ V}$, $I_C = 0.1\text{ mA}$, $f = 270\text{ Hz}$
Voltage feedback ratio	h_{re}	70	$\times 10^{-6}$	
Current transfer ratio	h_{fe}	130		
Output admittance	h_{oe}	11	μS	

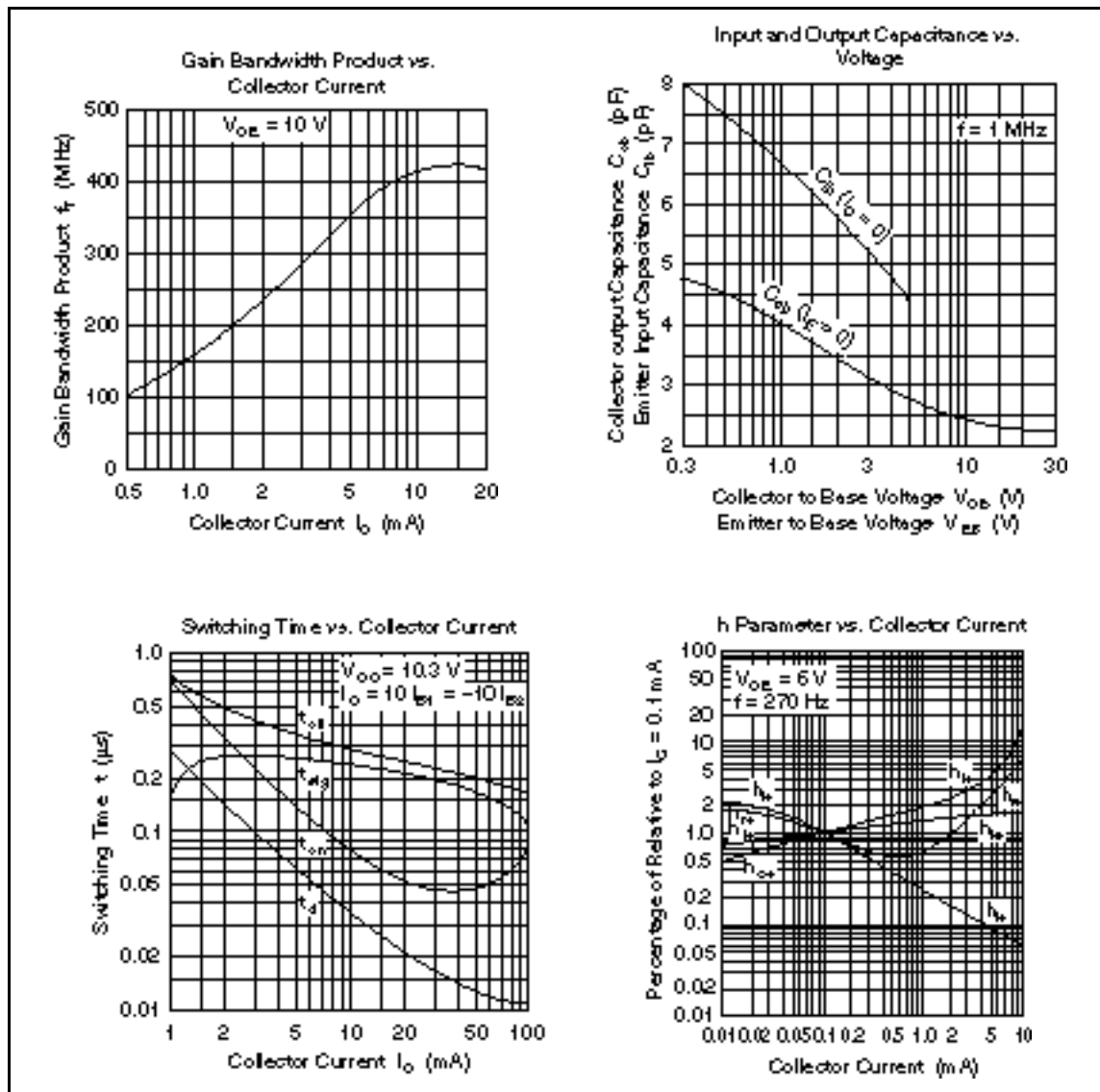


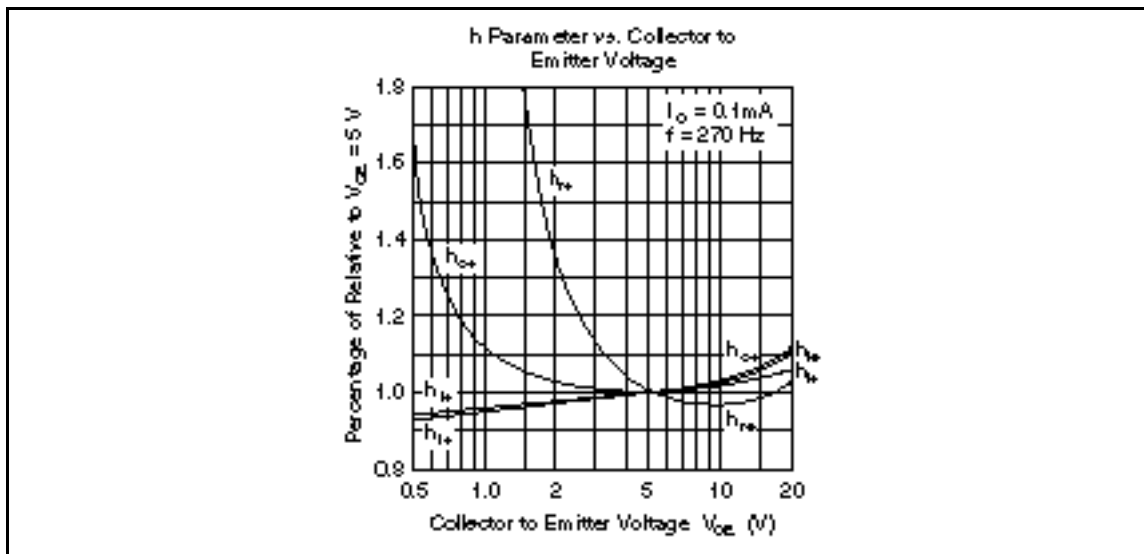
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